

UNIT

V

Ω

nC

N-Channel Power MOSFET

600V, 4.0A, 2.5Ω

FEATURES

- 100% Avalanche Tested
- Pb-free plating •
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition •

APPLICATION

- Power Supply
- Lighting







KEY PERFORMANCE PARAMETERS

VALUE

600

2.5

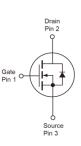
14.5

PARAMETER

 V_{DS}

R_{DS(on)} (max)

Qg



HALOGEN

Notes: MSL 3 (Moisture Sensitivity Level) for TO-252 (D-PAK) per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)						
PARAMETER		SYMBOL	IPAK/DPAK	ITO-220	UNIT	
Drain-Source Voltage		V _{DS}	600		V	
Gate-Source Voltage		V_{GS}	±30		V	
Continuous Drain Current (Note 1)	_c = 25°C		4.0		A	
T _c	c= 100°C	Ι _D	2.4			
Pulsed Drain Current (Note 2)		I _{DM}	16	i	А	
Total Power Dissipation @ T _C = 25°C		P _{DTOT}	50	25	W	
Single Pulsed Avalanche Energy (Note 3)		E _{AS}	70		mJ	
Single Pulsed Avalanche Current (Note 3)		I _{AS}	4		А	
Repetitive Avalanche Energy (Note 2)		E _{AR}	5		mJ	
Peak Diode Recovery (Note 4)		dV/dt	4.5		V/ns	
Operating Junction and Storage Temperatur	e Range	T _J , T _{STG}	- 55 to	+150	°C	

THERMAL PERFORMANCE				
PARAMETER	SYMBOL	IPAK/DPAK	ITO-220	UNIT
Junction to Case Thermal Resistance	R _{ejc}	2.5	5	°C/W
Junction to Ambient Thermal Resistance	R _{OJA}	83	62.5	°C/W

Notes: ReJA is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. R_{BJC} is guaranteed by design while R_{BCA} is determined by the user's board design. R_{0JA} shown below for single device operation on FR-4 PCB in still air.



Taiwan Semiconductor

ELECTRICAL SPECIFICA	TIONS (T _A = 25°C unles	s otherwise no	oted)			
PARAMETER	CONDITIONS	SYMBOL	MIN	ТҮР	MAX	UNIT
Static (Note 5)						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250 \mu A$	BV _{DSS}	600			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	V _{GS(TH)}	2.5	3.5	4.5	V
Gate Body Leakage	$V_{GS} = \pm 30V, V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 600V, V_{GS} = 0V$	I _{DSS}			1	μA
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 2.0A$	R _{DS(on)}		2.2	2.5	Ω
Forward Transfer Conductance	$V_{DS} = 40V, I_{D} = 2A$	g _{fs}		2.6		S
Dynamic ^(Note 6)						
Total Gate Charge		Q_g		14.5		
Gate-Source Charge	$V_{DS} = 480V, I_D = 4.0A,$	Q _{gs}		3.4		nC
Gate-Drain Charge	V _{GS} = 10V	Q _{gd}		7		
Input Capacitance		C _{iss}		500		
Output Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1.0MHz	C _{oss}		53.2		pF
Reverse Transfer Capacitance		C _{rss}		7		
Switching (Note 7)						
Turn-On Delay Time		t _{d(on)}		11		
Turn-On Rise Time	$V_{DD} = 300V,$	t _r		20		
Turn-Off Delay Time	R _{GEN} = 25Ω, I _D = 4.0A, V _{GS} = 10V,	t _{d(off)}		30		ns
Turn-Off Fall Time	$-10 - 4.0$, $v_{\rm GS} - 10$ v,	t _f		19		
Source-Drain Diode (Note 5)						
Forward On Voltage	$I_{\rm S} = 4.0$ A, $V_{\rm GS} = 0$ V	V_{SD}			1.13	V
Reverse Recovery Time	$V_{GS}=0V, I_{S}=2A$	t _{rr}		522		ns
Reverse Recovery Charge	$dI_F/dt = 100A/\mu s$	Q _{rr}		1.6		μC
Source Current	Integral reverse diode	I _S			4	А
Source Current (Pulse)	in the MOSFET	I _{SM}			16	А

Notes:

- 1. Current limited by package.
- 2. Pulse width limited by the maximum junction temperature.
- 3. L = 8mH, I_{AS} = 4.0A, V_{DD} = 50V, R_G = 25 Ω , Starting T_J = 25°C.

100% Eas Test Condition: L = 8mH, I_{AS} = 2A, V_{DD} = 50V, R_G = 25 Ω , Starting T_J = 25°C

- 4. $I_{SD} \le 4A$, dI/dt $\le 200A/\mu s$, $V_{DD} \le BV_{DSS}$, Starting $T_J = 25^{\circ}C$.
- 5. Pulse test: $PW \le 300\mu s$, duty cycle $\le 2\%$.
- 6. For DESIGN AID ONLY, not subject to production testing.
- 7. Switching time is essentially independent of operating temperature.



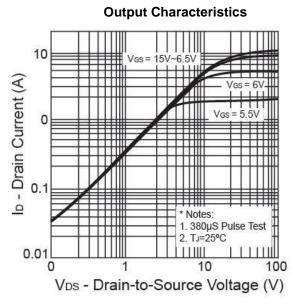
ORDERING INFORMATION

ORDERING CODE	PACKAGE	PACKING
TSM4NB60CI C0G	ITO-220	50pcs / Tube
TSM4NB60CH C5G	TO-251 (IPAK)	75pcs / Tube
TSM4NB60CH X0G	TO-251S (IPAK SL)	75pcs / Tube
TSM4NB60CP ROG	TO-252 (DPAK)	2,500pcs / 13" Reel

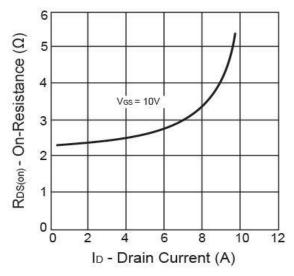


CHARACTERISTICS CURVES

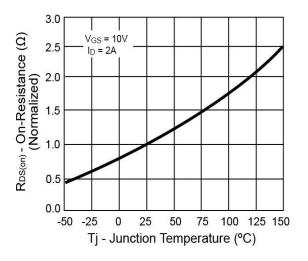
(T_C = 25°C unless otherwise noted)

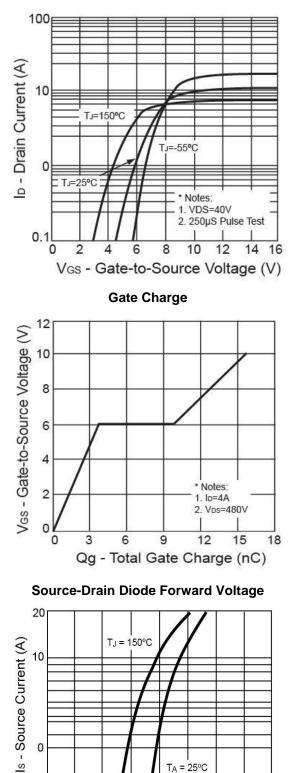


On-Resistance vs. Drain Current



On-Resistance vs. Junction Temperature





Transfer Characteristics

1.4

1.6

Version: L1901

1.2

T_A = 25°C

1.0

Vsp - Source-to-Drain Voltage (V)

0.1∟ 0

0.4

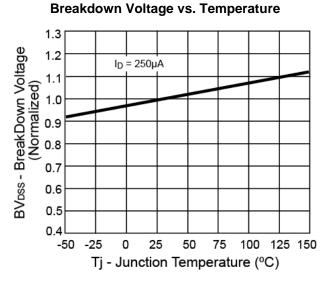
0.2

0.6 0.8

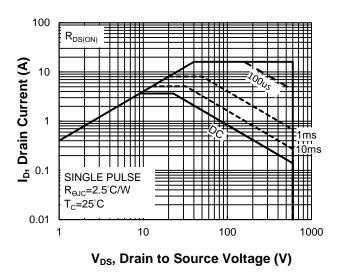


CHARACTERISTICS CURVES

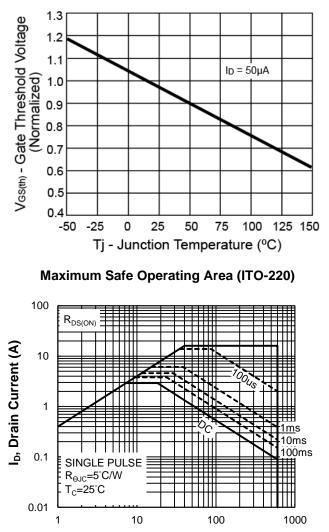
 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$



Maximum Safe Operating Area (IPAK/DPAK)



Threshold Voltage vs. Temperature



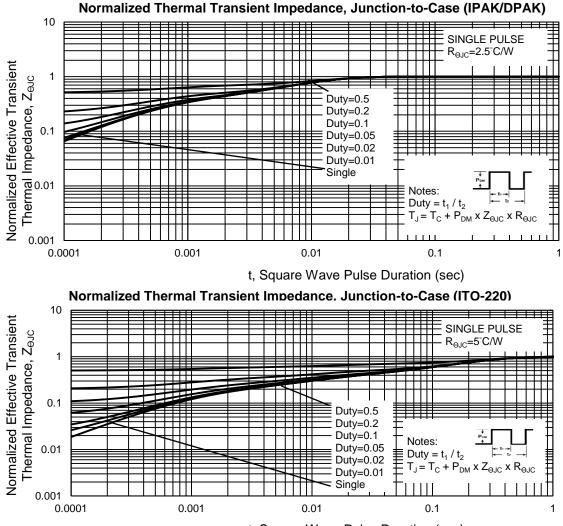
V_{DS}, Drain to Source Voltage (V)





ELECTRICAL CHARACTERISTICS CURVES

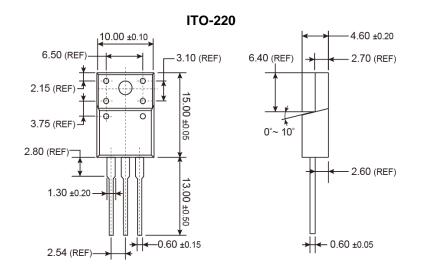
 $(T_c = 25^{\circ}C \text{ unless otherwise noted})$



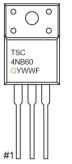
t, Square Wave Pulse Duration (sec)



PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



MARKING DIAGRAM



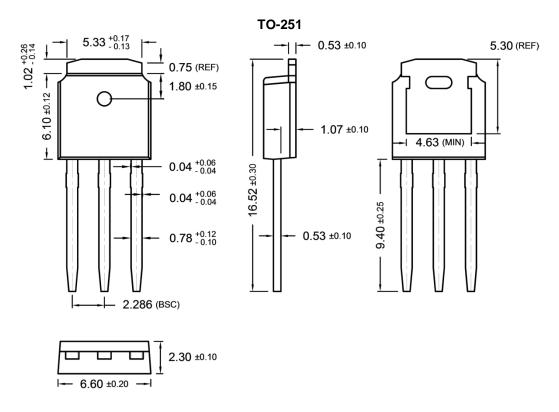
- **G** = Halogen Free
- Y = Year Code
- WW = Week Code (01~52)
 - **F** = Factory Code





TAIWAN SEMICONDUCTOR

95



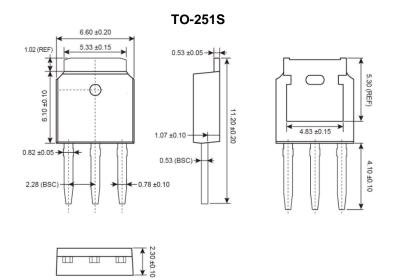
MARKING DIAGRAM

5 0 4NB60	Y = Year CodeM = Month Code for Halogen Free Product
YML CH	O =Jan P =Feb Q =Mar R =Apr
	S =May T =Jun U =Jul V =Aug
	W =Sep X =Oct Y =Nov Z =Dec
	L = Lot Code (1~9, A~Z)

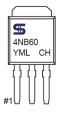




PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



MARKING DIAGRAM



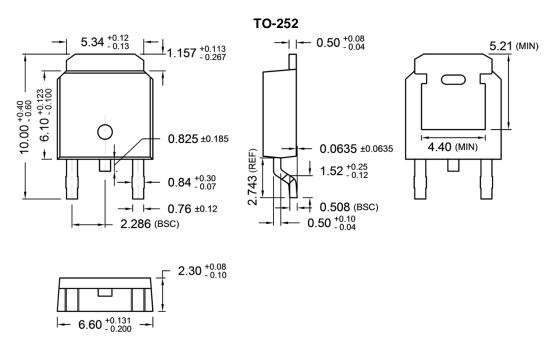
- Y = Year Code
- M = Month Code for Halogen Free Product
- **L** = Lot Code (1~9, A~Z)



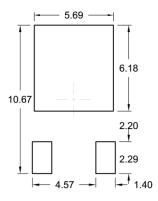


TAIWAN SEMICONDUCTOR

9h



SUGGESTED PAD LAYOUT (Unit: Millimeters)



MARKING DIAGRAM

5	Y = Year CodeM = Month Code for Halogen Free Product	
4NB60 YMLOCP	O =Jan P =Feb Q =Mar R	=Apr
	S =May T =Jun U =Jul V	=Aug
	W =Sep X =Oct Y =Nov Z	=Dec
<i>••</i> 1	L = Lot Code (1~9, A~Z)	



Taiwan Semiconductor

Notice

Specifications of the products displayed herein are subject to change without notice. TSC or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies.

Information contained herein is intended to provide a product description only. No license, express or implied, to any intellectual property rights is granted by this document. Except as provided in TSC's terms and conditions of sale for such products, TSC assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of TSC products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify TSC for any damages resulting from such improper use or sale.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by Taiwan Semiconductor manufacturer:

Other Similar products are found below :

614233C 648584F IRFD120 JANTX2N5237 FCA20N60_F109 FDZ595PZ 2SK2545(Q,T) 405094E 423220D TPCC8103,L1Q(CM MIC4420CM-TR VN1206L SBVS138LT1G 614234A 715780A NTNS3166NZT5G SSM6J414TU,LF(T 751625C BUK954R8-60E DMN3404LQ-7 NTE6400 SQJ402EP-T1-GE3 2SK2614(TE16L1,Q) 2N7002KW-FAI DMN1017UCP3-7 EFC2J004NUZTDG ECH8691-TL-W FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7 NTE221 NTE2384 NTE2903 NTE2941 NTE2945 NTE2946 NTE2960 NTE2967 NTE2969 NTE2976 NTE455 NTE6400A NTE2910 NTE2916 NTE2956 NTE2911 DMN2080UCB4-7 TK10A80W,S4X(S SSM6P69NU,LF DMP22D4UFO-7B